



(51) International Patent Classification:
H01L 27/04 (2006.01)

(21) International Application Number:
PCT/US2009/044365

(22) International Filing Date:
18 May 2009 (18.05.2009)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
0803697 30 June 2008 (30.06.2008) FR
61/093,920 3 September 2008 (03.09.2008) US

(71) Applicant (for all designated States except US):
S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES [FR/FR]; Parc Technologique Des Fontaines, F-38190 Bernin (FR).

(72) Inventor; and

(75) Inventor/Applicant (for US only): **NGUYEN, Bich-Yen** [US/US]; 110 S. Laurelwood Drive, Austin, TX 78733 (US).

(74) Agents: **FANUCCI, Allan, A.** et al.; Winston & Strawn LLP, Patent Department, 1700 K Street, N.W., Washington, DC 20006-3817 (US).

(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Declarations under Rule 4.17:

— of inventorship (Rule 4.17(iv))

Published:

— with international search report (Art. 21(3))

(54) Title: SUBSTRATE COMPRISING DIFFERENT TYPES OF SURFACES AND METHOD FOR OBTAINING SUCH SUBSTRATES

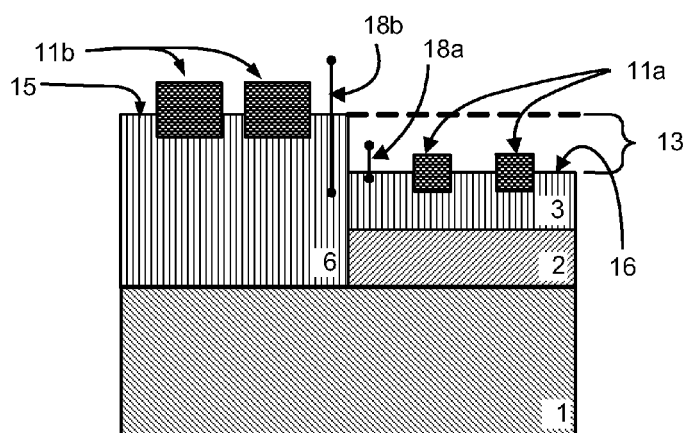


Figure 15

(57) Abstract: A support having a larger density of crystalline defects, an insulating layer disposed on a first region of a front face of the support, and a superficial layer disposed on the insulating layer. An additional layer can be disposed at least on a second region of the front face of the support has a thickness sufficient to bury crystalline defects of the support. A substrate can also include an epitaxial layer arranged at least over the first region of the front face of the support, between the support and the insulation layer. Also, a method of making the substrate by forming a masking layer on the first region of the superficial layer and removing the superficial layer and the insulating layer in the second region uncovered by the masking layer. The additional layer is formed in the second region and then planarized.

